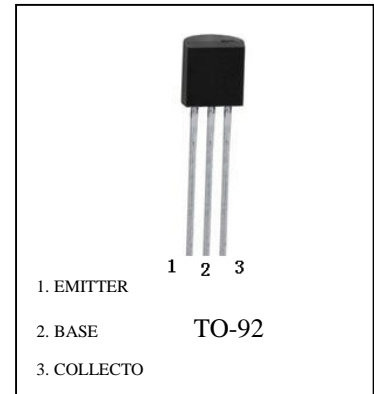


**FEATURES**

High voltage

**MARKING:A94**
**MAXIMUM RATINGS (TA=25 °C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-400	V
Collector-Emitter Voltage	$V_{CEO}$	-400	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_C$	-200	mA
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55-150	°C

**A94 (PNP)**

**ELECTRICAL CHARACTERISTICS (Tamb=25 °C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = -100\mu A, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = -1mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -400V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -400V$			-5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -10mA$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	70			
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -100mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.2	V
	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.75	V
Transition frequency	$f_T$	$V_{CE} = -20V, I_C = -10mA, f = 30MHz$	50			MHz

**CLASSIFICATION OF HFE**

Rank	A	B1	B2	C
Range	80-100	100-150	150-200	200-250

A94 Typical Characteristics

